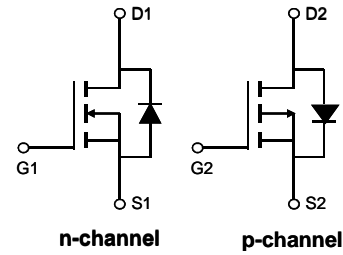


General Description

The AO6604 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.



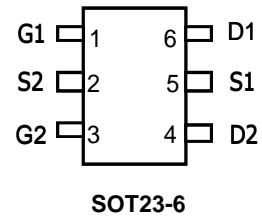
Product Summary

N-Ch:

- $V_{DS} (V)=20V$
- $R_{DS(ON)} < 65m\Omega$ ($V_{GS} = 4.5V$)
- $R_{DS(ON)} < 75 m\Omega$ ($V_{GS} = 2.5V$)
- $R_{DS(ON)} < 100m\Omega$ ($V_{GS} = 1.8V$)

P-Ch:

- $V_{DS} (V)=-20V$
- $R_{DS(ON)} < 75m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 95m\Omega$ ($V_{GS} = -2.5V$)
- $R_{DS(ON)} < 115m\Omega$ ($V_{GS} = -1.8V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units	
Drain-Source Voltage	V_{DS}	20	-20	V	
Gate-Source Voltage	V_{GS}	± 8	± 8	V	
Continuous Drain Current	I_D	$T_A=25^\circ C$	3.4	-2.5	A
		$T_A=70^\circ C$	2.5	-2	
Pulsed Drain Current ^C	I_{DM}	13	-13		
Power Dissipation ^B	P_D	$T_A=25^\circ C$	1.1	1.1	W
		$T_A=70^\circ C$	0.7	0.7	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$	

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	78	110	$^\circ C/W$
Maximum Junction-to-Ambient ^{A D}	Steady-State		106	150	$^\circ C/W$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	64	80	$^\circ C/W$

N-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.4	0.7	1	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	13			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =3.4A		51	65	mΩ
		V _{GS} =2.5V, I _D =3A		58	75	mΩ
		V _{GS} =1.8V, I _D =2A		68	100	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3.4A		16		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz	205	260	320	pF
C _{oss}	Output Capacitance		33	48	63	pF
C _{riss}	Reverse Transfer Capacitance		16	27	38	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.5	3	4.5	Ω
SWITCHING PARAMETERS						
Q _{g(4.5V)}	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =3.4A		2.9	3.8	nC
Q _{gs}	Gate Source Charge		0.4		nC	
Q _{gd}	Gate Drain Charge		0.6		nC	
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =2.95Ω, R _{GEN} =3Ω		2.5		ns
t _r	Turn-On Rise Time		3.2		ns	
t _{D(off)}	Turn-Off DelayTime		21		ns	
t _f	Turn-Off Fall Time		3		ns	
t _{rr}	Body Diode Reverse Recovery Time	I _F =3.4A, dI/dt=100A/μs		14	19	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3.4A, dI/dt=100A/μs		3.8		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

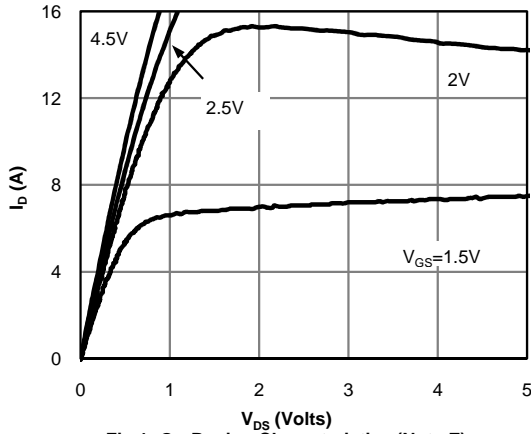


Fig 1: On-Region Characteristics (Note E)

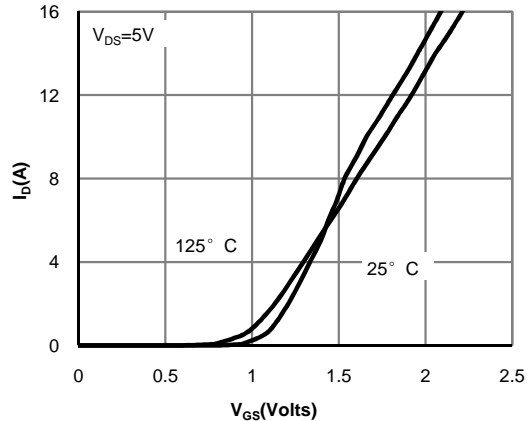


Figure 2: Transfer Characteristics (Note E)

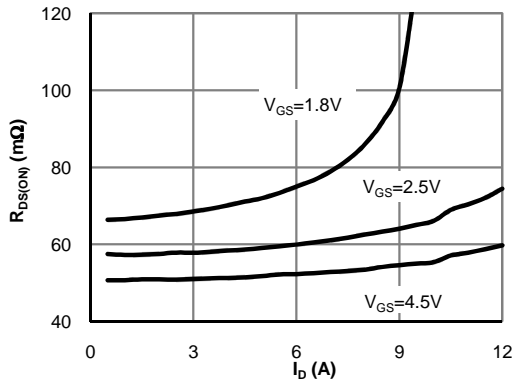


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

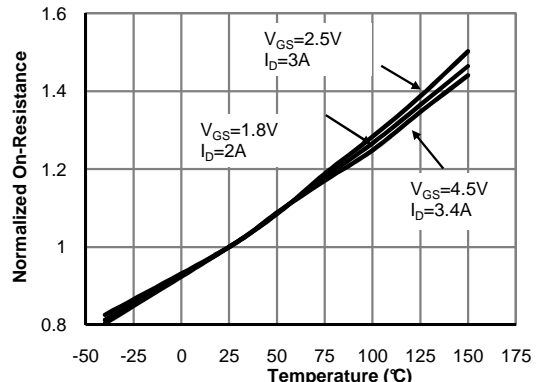


Figure 4: On-Resistance vs. Junction Temperature (Note E)

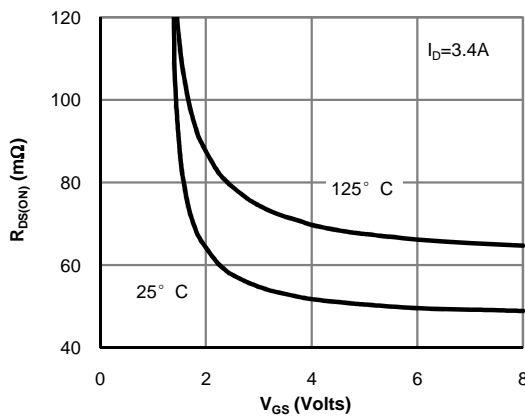


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

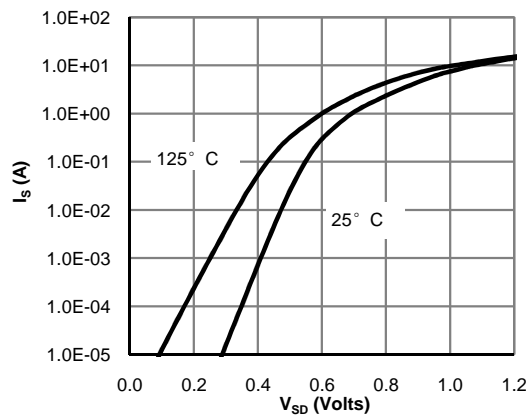


Figure 6: Body-Diode Characteristics (Note E)

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

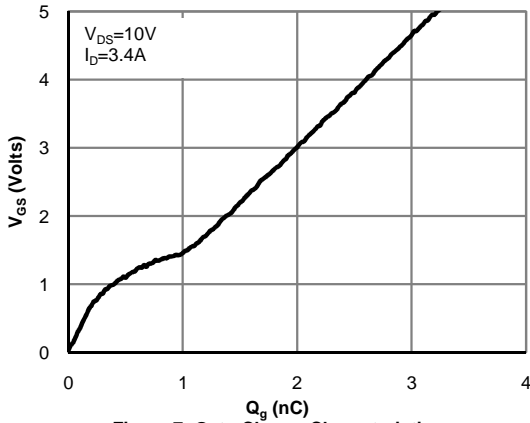


Figure 7: Gate-Charge Characteristics

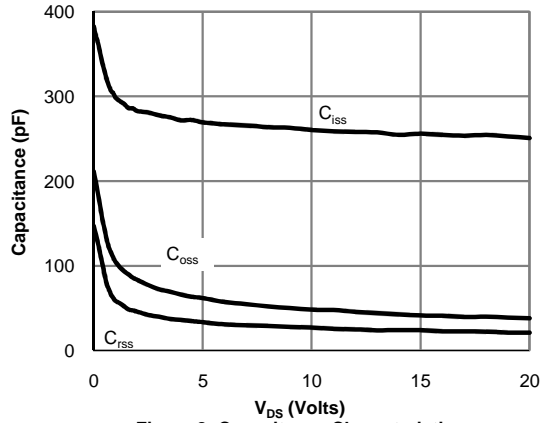


Figure 8: Capacitance Characteristics

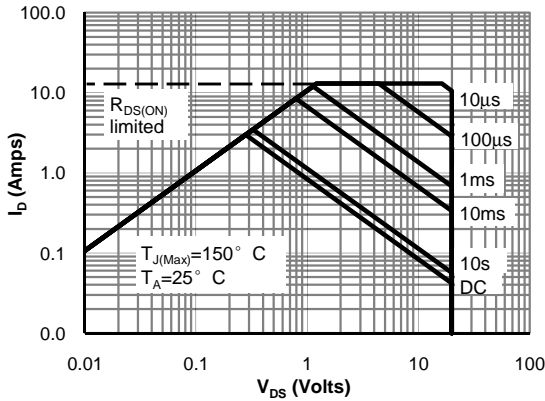


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

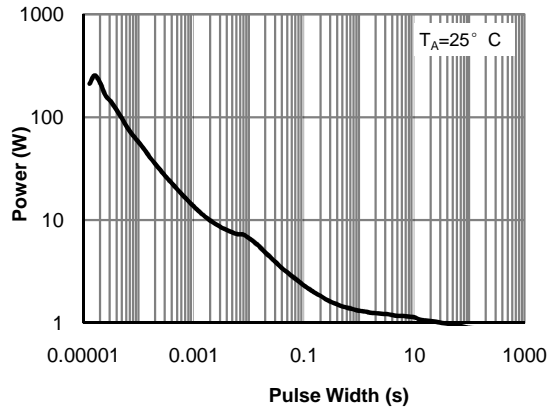


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

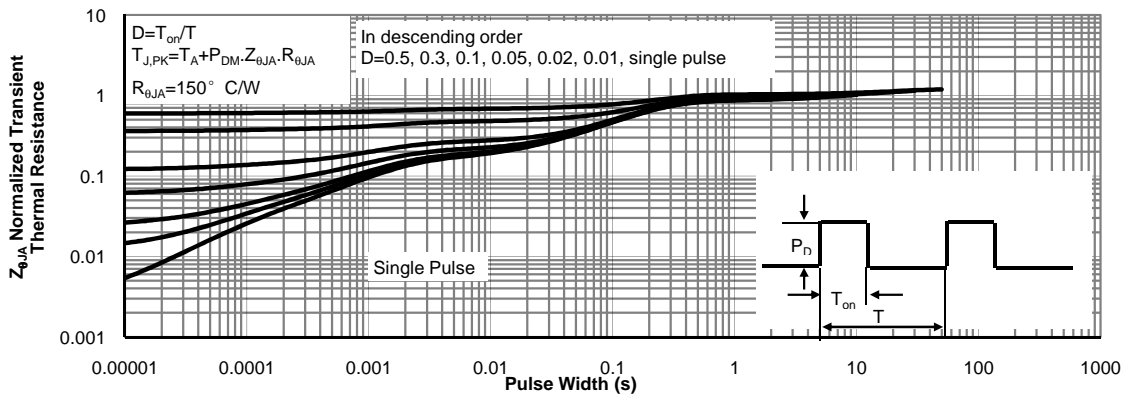
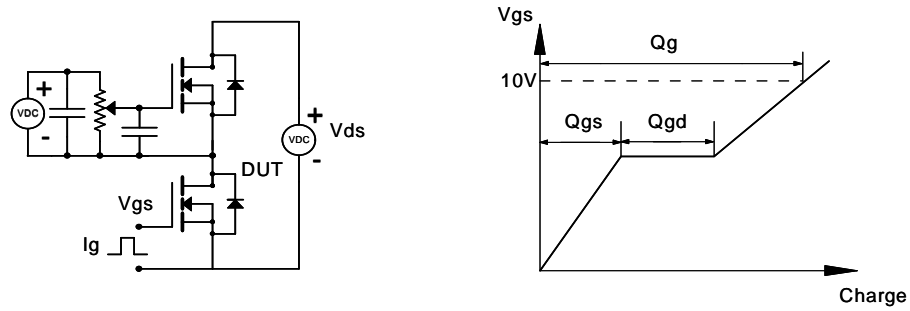
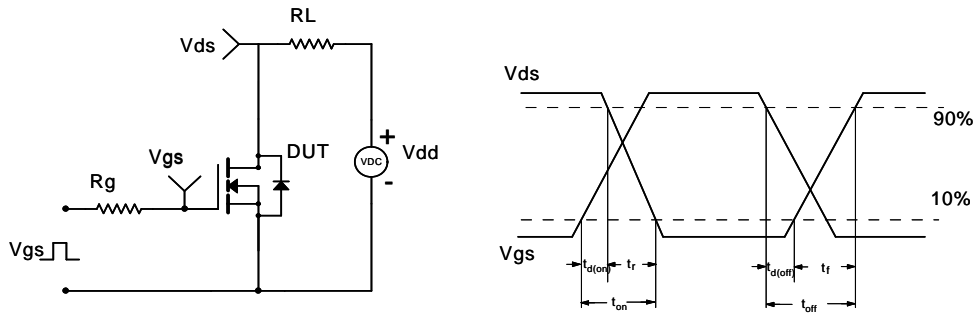


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

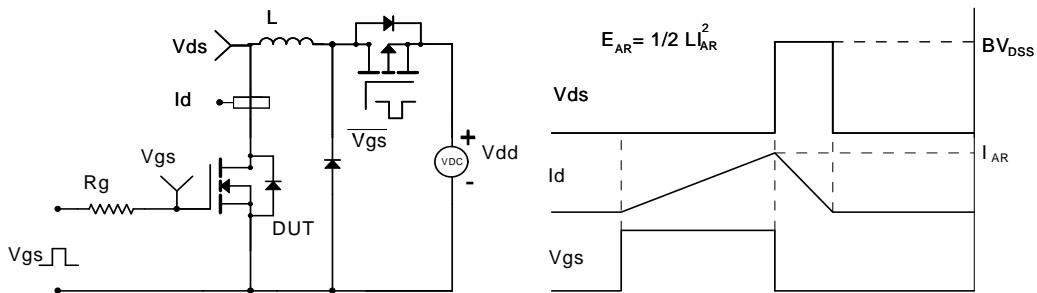
Gate Charge Test Circuit & Waveform



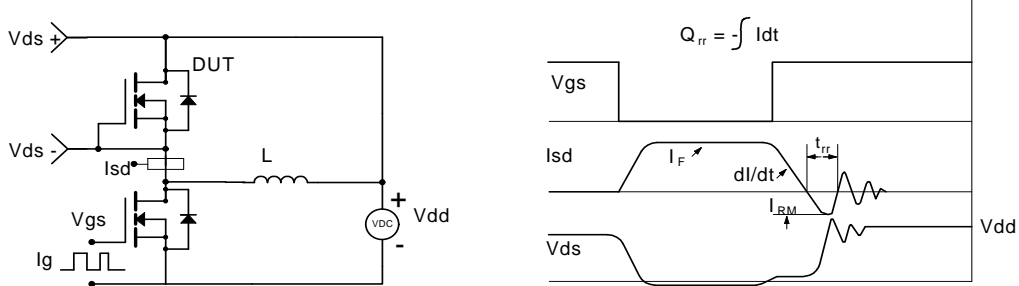
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.65	-1	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-13			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-2.5A		56	75	mΩ
		V _{GS} =-2.5V, I _D =-2A		70	95	mΩ
		V _{GS} =-1.8V, I _D =-1A		85	115	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-2.5A		13		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		560	745	pF
C _{oss}	Output Capacitance			80		pF
C _{riss}	Reverse Transfer Capacitance			70		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		15	23	Ω
SWITCHING PARAMETERS						
Q _{g(4.5V)}	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-2.5A		8.5	11	nC
Q _{gs}	Gate Source Charge			1.2		nC
Q _{gd}	Gate Drain Charge			2.1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =4Ω, R _{GEN} =6Ω		7.2		ns
t _r	Turn-On Rise Time			36		ns
t _{D(off)}	Turn-Off DelayTime			53		ns
t _f	Turn-Off Fall Time			56		ns
t _{rr}	Body Diode Reverse Recovery Time		I _F =-2.5A, dI/dt=100A/μs		37	49
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-2.5A, dI/dt=100A/μs		27		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

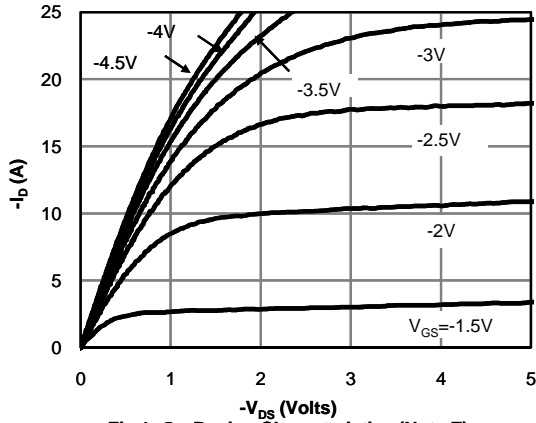


Fig 1: On-Region Characteristics (Note E)

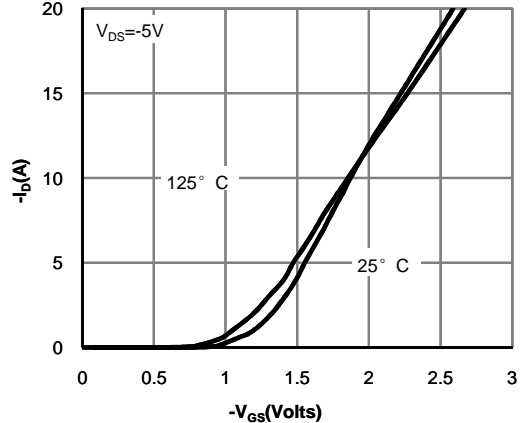


Figure 2: Transfer Characteristics (Note E)

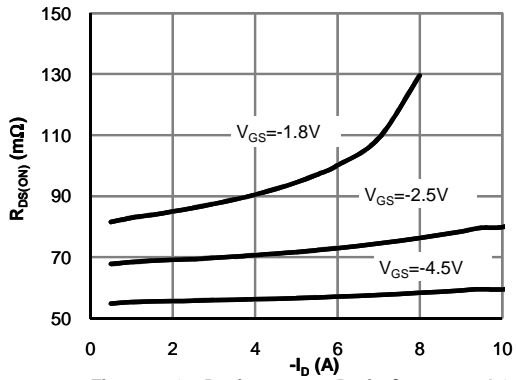


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

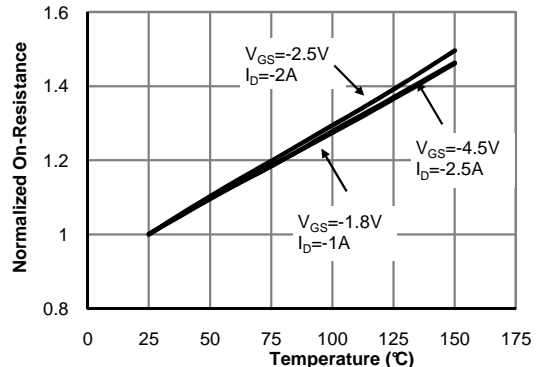


Figure 4: On-Resistance vs. Junction Temperature (Note E)

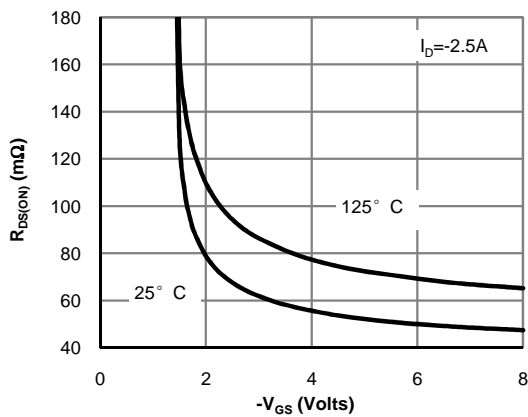


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

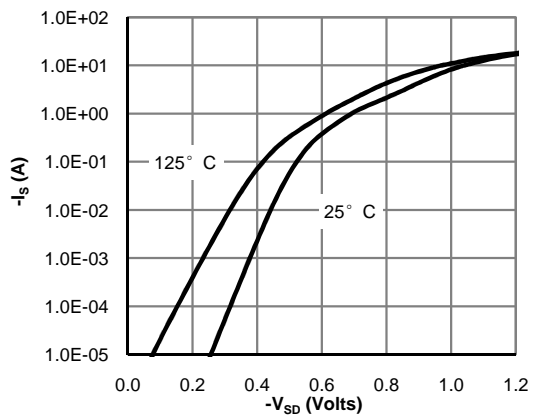


Figure 6: Body-Diode Characteristics (Note E)

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

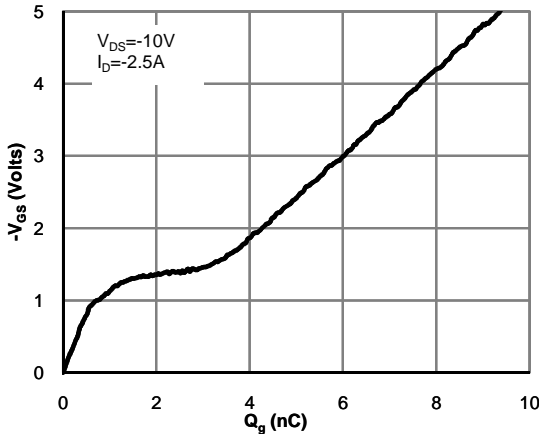


Figure 7: Gate-Charge Characteristics

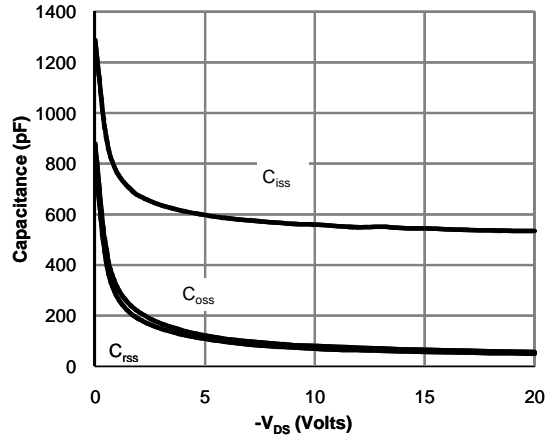


Figure 8: Capacitance Characteristics

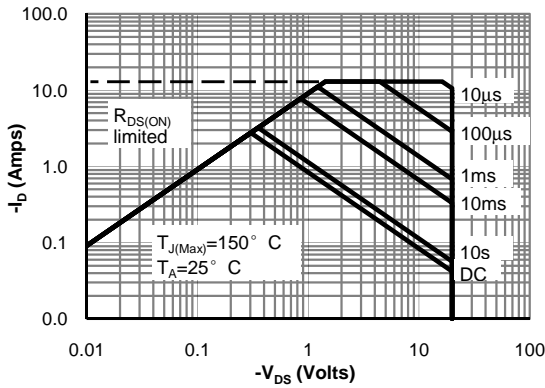


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

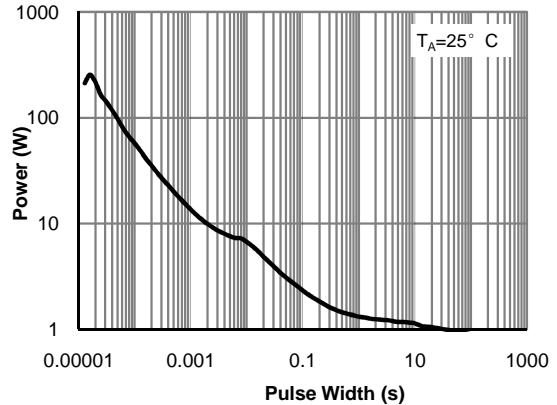


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

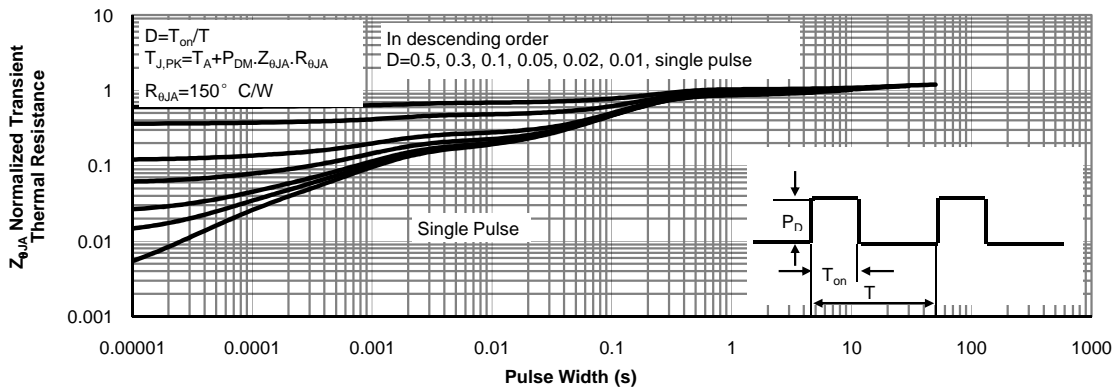
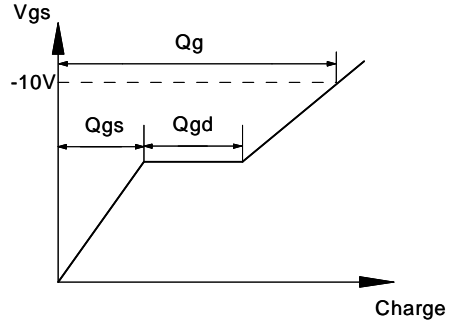
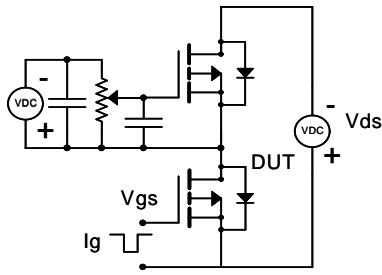


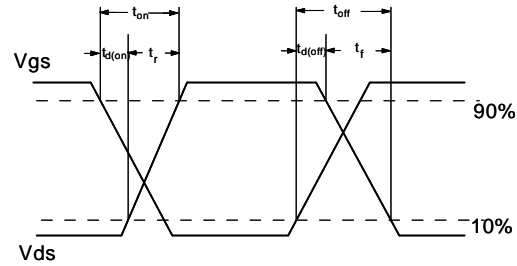
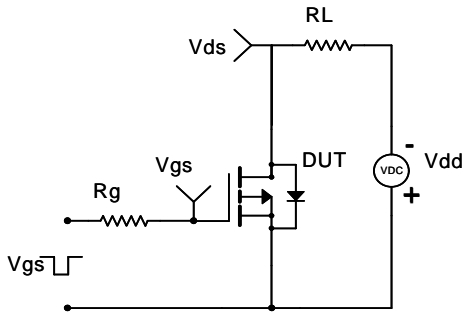
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform

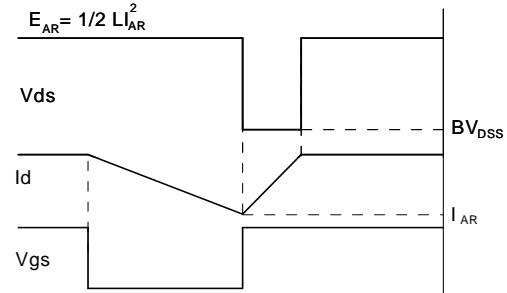
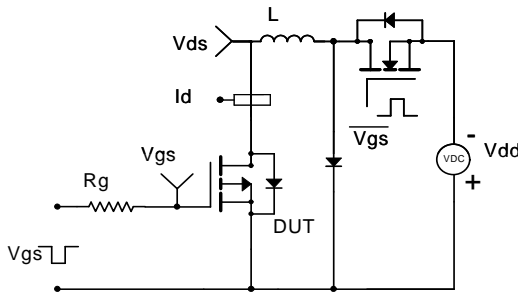
N+ P Channel MOSFET



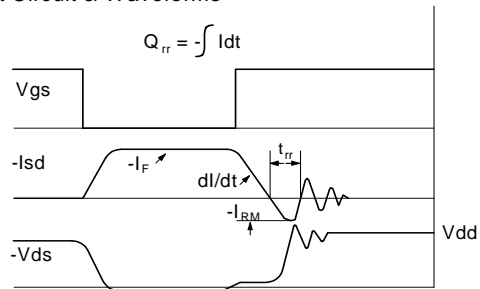
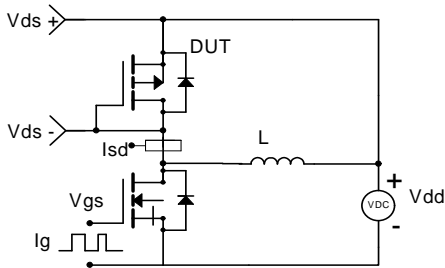
Resistive Switching Test Circuit & Waveforms



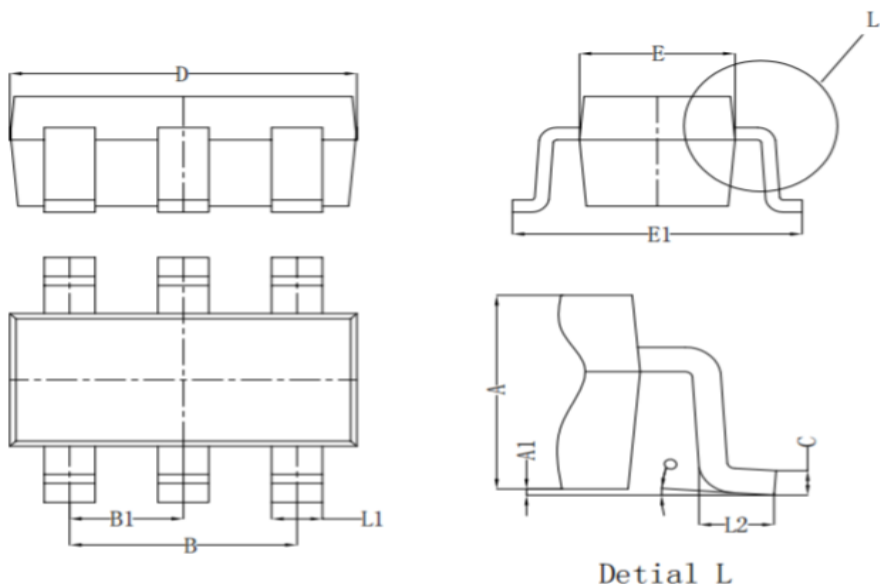
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

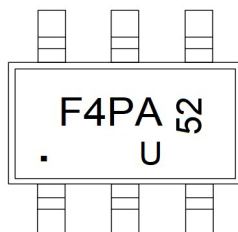


SOT23- 6 PACKAGE OUTLIE DIMENSIONS



Symbol	Dim in mm		
	Min	Nor	Max
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.300	0.450	0.600
o	0°	4°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
AO6604	SOT23-6	3000	Tape and reel